



Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from,Europe,America and south Asia,supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of “Quality Parts,Customers Priority,Honest Operation,and Considerate Service”,our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip,ALPS,ROHM,Xilinx,Pulse,ON,Everlight and Freescale. Main products comprise IC,Modules,Potentiometer,IC Socket,Relay,Connector.Our parts cover such applications as commercial,industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



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NJT4031N, NJV4031NT1G, NJV4031NT3G

Bipolar Power Transistors

NPN Silicon

Features

- Epoxy Meets UL 94, V-0 @ 0.125 in
- NJV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

MAXIMUM RATINGS (T_C = 25°C unless otherwise noted)

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V _{CEO}	40	Vdc
Collector-Base Voltage	V _{CB}	40	Vdc
Emitter-Base Voltage	V _{EB}	6.0	Vdc
Base Current - Continuous	I _B	1.0	Adc
Collector Current - Continuous	I _C	3.0	Adc
Collector Current - Peak	I _{CM}	5.0	Adc
ESD - Human Body Model	HBM	3B	V
ESD - Machine Model	MM	C	V

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Power Dissipation Total P _D @ T _A = 25°C (Note 1) Total P _D @ T _A = 25°C (Note 2)	P _D	2.0 0.80	W
Thermal Resistance, Junction-to-Case Junction-to-Ambient (Note 1) Junction-to-Ambient (Note 2)	R _{θJA} R _{θJA}	64 155	°C/W
Maximum Lead Temperature for Soldering Purposes, 1/8" from case for 5 seconds	T _L	260	°C
Operating and Storage Junction Temperature Range	T _J , T _{stg}	-55 to +150	°C

1. Mounted on 1" sq. (645 sq. mm) Collector pad on FR-4 bd material.

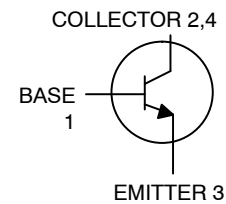
2. Mounted on 0.012" sq. (7.6 sq. mm) Collector pad on FR-4 bd material.



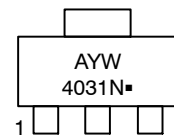
ON Semiconductor®

<http://onsemi.com>

NPN TRANSISTOR 3.0 AMPERES 40 VOLTS, 2.0 WATTS



MARKING DIAGRAM



A = Assembly Location
Y = Year
W = Work Week
4031N = Specific Device Code
■ = Pb-Free Package

ORDERING INFORMATION

Device	Package	Shipping†
NJT4031NT1G	SOT-223 (Pb-Free)	1000 / Tape & Reel
NJV4031NT1G		
NJT4031NT3G	SOT-223 (Pb-Free)	4000 / Tape & Reel
NJV4031NT3G		

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

NJT4031N, NJV4031NT1G, NJV4031NT3G

ELECTRICAL CHARACTERISTICS ($T_C = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
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OFF CHARACTERISTICS

Collector–Emitter Sustaining Voltage ($I_C = 10\text{ mA}$, $I_B = 0\text{ A}$)	$V_{CEO(sus)}$	40	–	–	Vdc
Emitter–Base Voltage ($I_E = 50\text{ }\mu\text{A}$, $I_C = 0\text{ A}$)	V_{EBO}	6.0	–	–	Vdc
Collector Cutoff Current ($V_{CB} = 40\text{ Vdc}$)	I_{CBO}	–	–	100	nAdc
Emitter Cutoff Current ($V_{BE} = 6.0\text{ Vdc}$)	I_{EBO}	–	–	100	nAdc

ON CHARACTERISTICS (Note 3)

Collector–Emitter Saturation Voltage ($I_C = 0.5\text{ A}$, $I_B = 5.0\text{ mA}$) ($I_C = 1.0\text{ A}$, $I_B = 10\text{ mA}$) ($I_C = 3.0\text{ A}$, $I_B = 0.3\text{ A}$)	$V_{CE(sat)}$	–	–	0.100 0.150 0.300	Vdc
Base–Emitter Saturation Voltage ($I_C = 1.0\text{ A}$, $I_B = 0.1\text{ A}$)	$V_{BE(sat)}$	–	–	1.0	Vdc
Base–Emitter On Voltage ($I_C = 1.0\text{ A}$, $V_{CE} = 2.0\text{ Vdc}$)	$V_{BE(on)}$	–	–	1.0	Vdc
DC Current Gain ($I_C = 0.5\text{ A}$, $V_{CE} = 1.0\text{ Vdc}$) ($I_C = 1.0\text{ A}$, $V_{CE} = 1.0\text{ Vdc}$) ($I_C = 3.0\text{ A}$, $V_{CE} = 1.0\text{ Vdc}$)	h_{FE}	220 200 100	– – –	500	

DYNAMIC CHARACTERISTICS

Output Capacitance ($V_{CB} = 10\text{ Vdc}$, $f = 1.0\text{ MHz}$)	C_{ob}	–	25	–	pF
Input Capacitance ($V_{EB} = 5.0\text{ Vdc}$, $f = 1.0\text{ MHz}$)	C_{ib}	–	170	–	pF
Current–Gain – Bandwidth Product (Note 4) ($I_C = 500\text{ mA}$, $V_{CE} = 10\text{ V}$, $f_{test} = 1.0\text{ MHz}$)	f_T	–	215	–	MHz

3. Pulse Test: Pulse Width $\leq 300\text{ }\mu\text{s}$, Duty Cycle $\leq 2\%$.

4. $f_T = |h_{FE}| \cdot f_{test}$

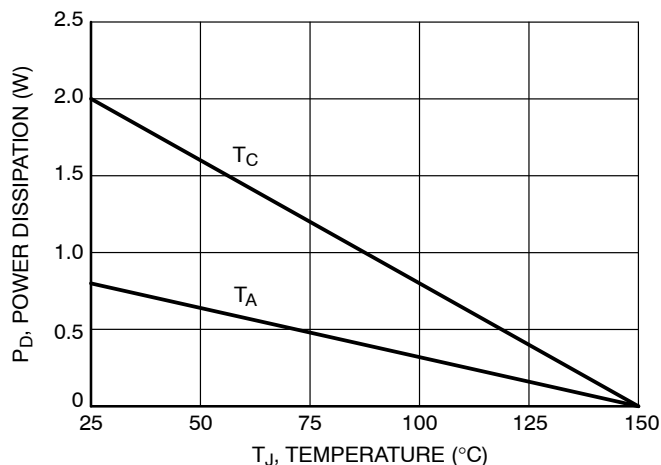


Figure 1. Power Derating

TYPICAL CHARACTERISTICS

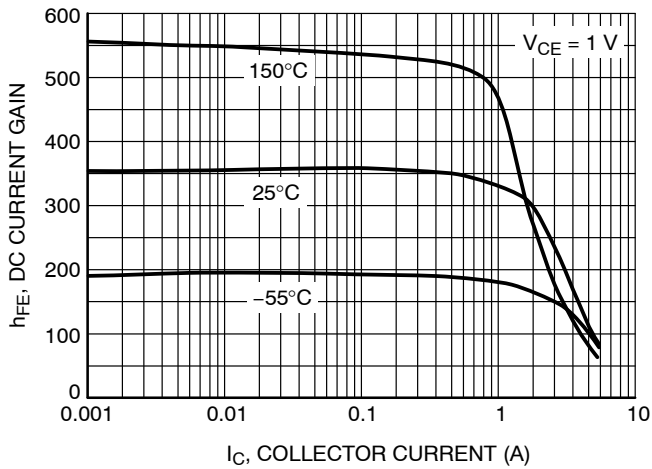


Figure 2. DC Current Gain

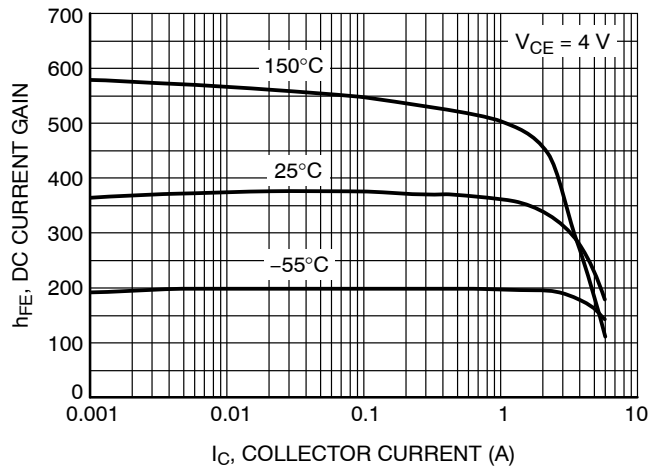


Figure 3. DC Current Gain

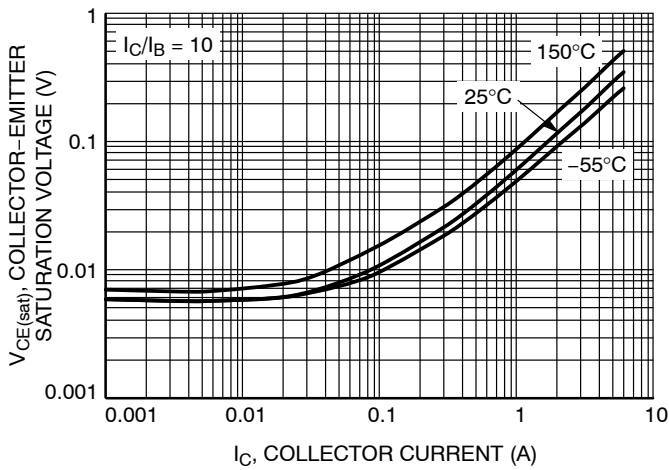


Figure 4. Collector-Emitter Saturation Voltage

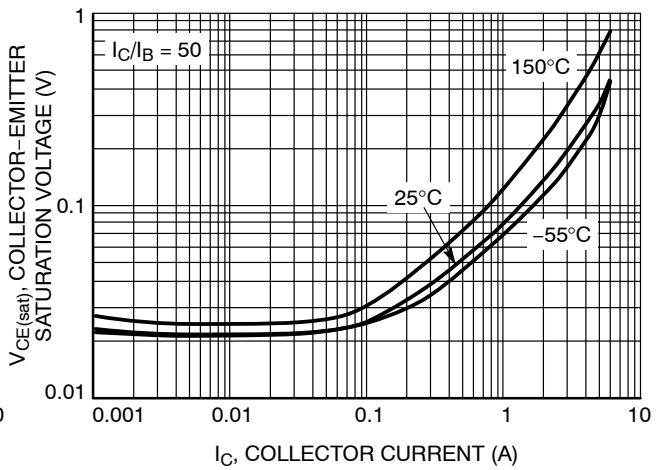


Figure 5. Collector-Emitter Saturation Voltage

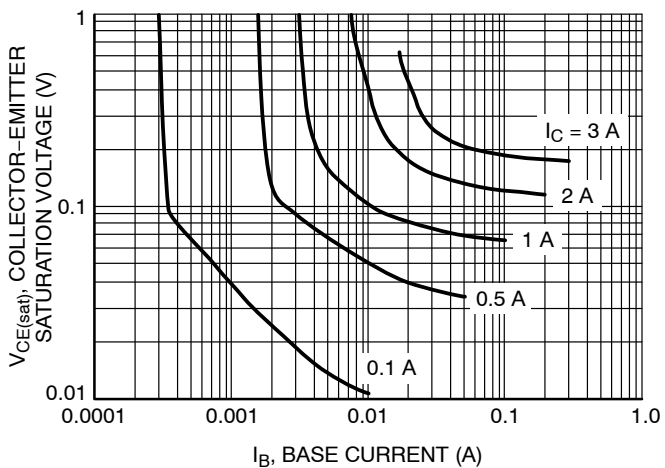


Figure 6. Collector Saturation Region

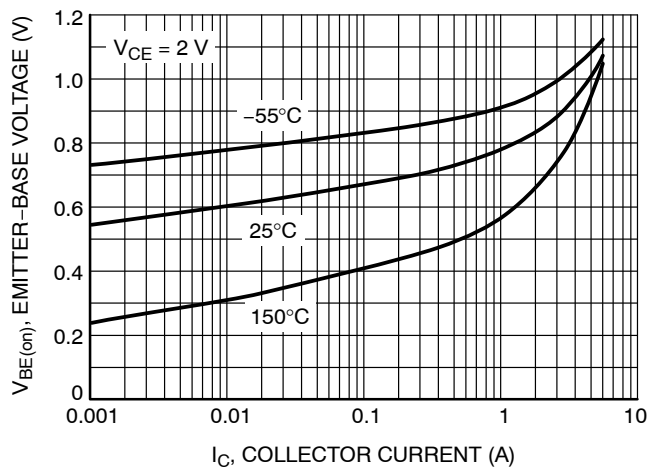


Figure 7. $V_{BE(on)}$ Voltage

TYPICAL CHARACTERISTICS

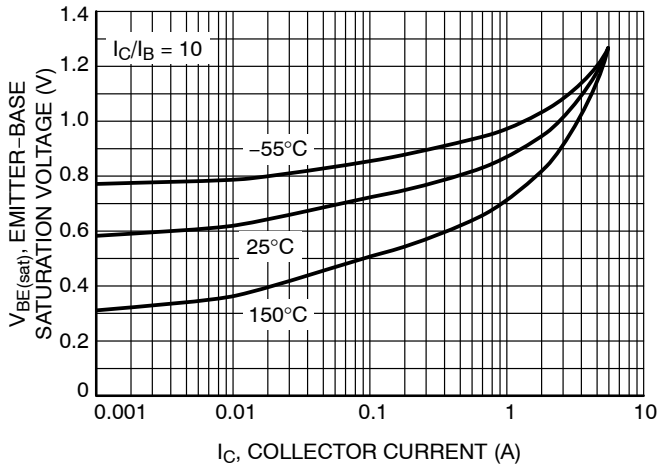


Figure 8. Base-Emitter Saturation Voltage

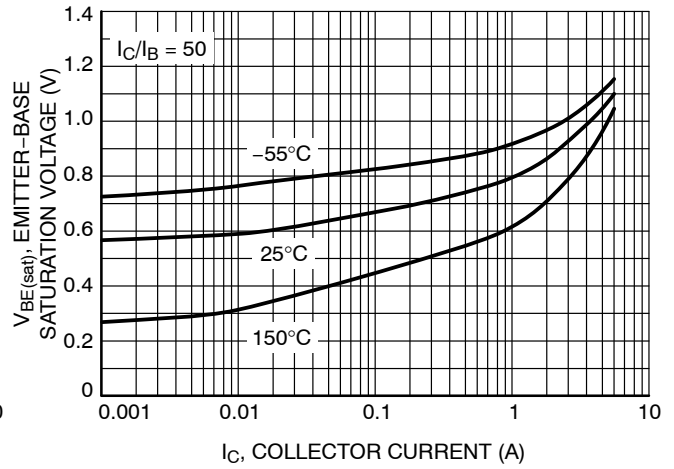


Figure 9. Base-Emitter Saturation Voltage

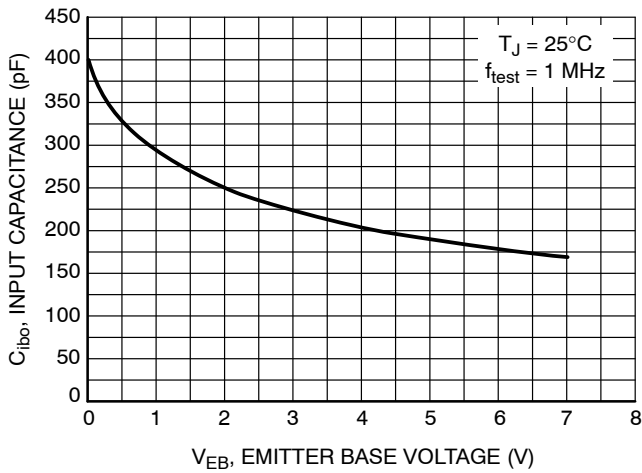


Figure 10. Input Capacitance

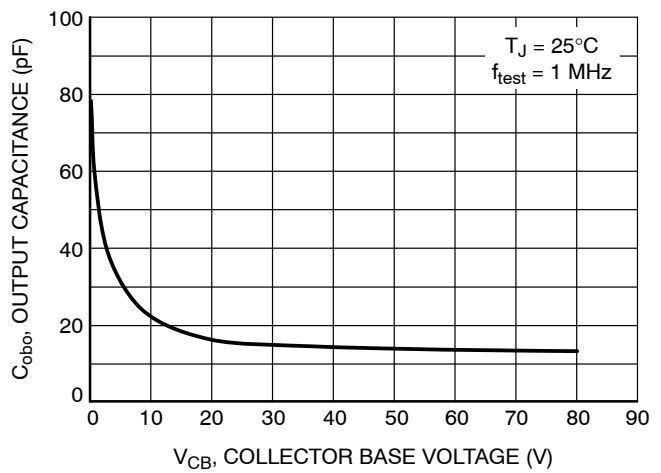


Figure 11. Output Capacitance

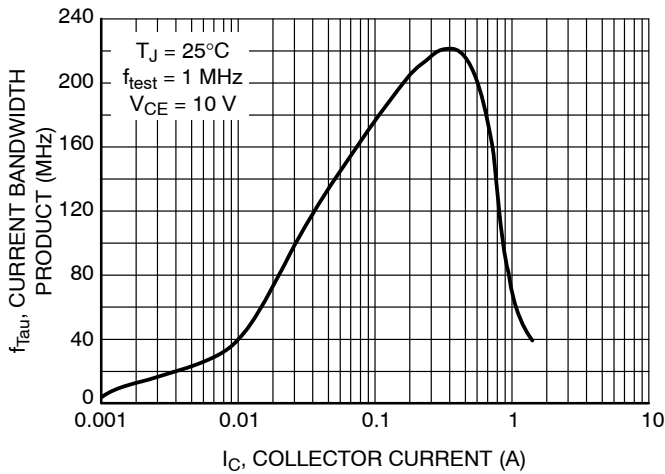


Figure 12. Current-Gain Bandwidth Product

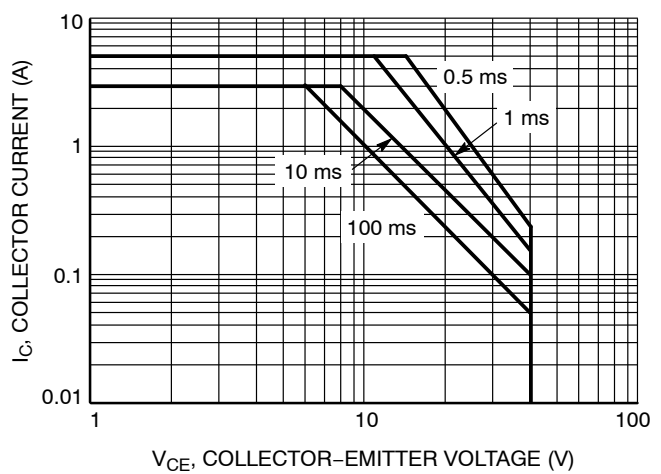
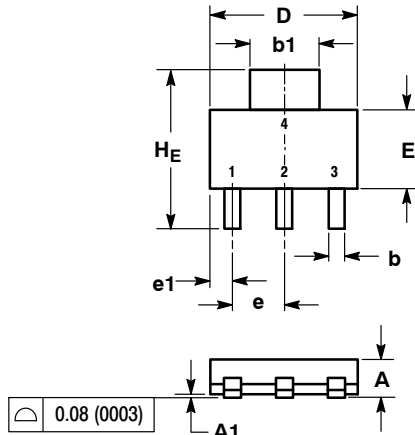


Figure 13. Safe Operating Area

NJT4031N, NJV4031NT1G, NJV4031NT3G

PACKAGE DIMENSIONS

SOT-223 (TO-261)
CASE 318E-04
ISSUE N

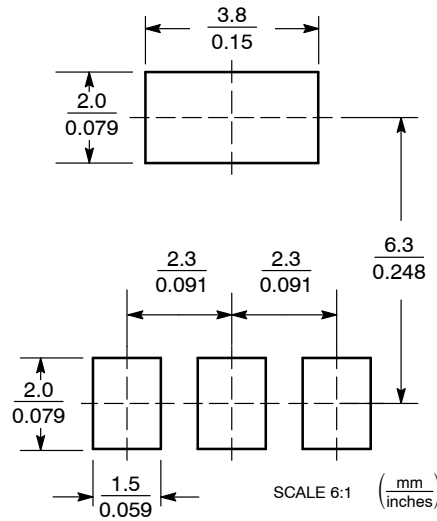


NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: INCH.

DIM	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	1.50	1.63	1.75	0.060	0.064	0.068
A1	0.02	0.06	0.10	0.001	0.002	0.004
b	0.60	0.75	0.89	0.024	0.030	0.035
b1	2.90	3.06	3.20	0.115	0.121	0.126
c	0.24	0.29	0.35	0.009	0.012	0.014
D	6.30	6.50	6.70	0.249	0.256	0.263
E	3.30	3.50	3.70	0.130	0.138	0.145
e	2.20	2.30	2.40	0.087	0.091	0.094
e1	0.85	0.94	1.05	0.033	0.037	0.041
L	0.20	---	---	0.008	---	---
L1	1.50	1.75	2.00	0.060	0.069	0.078
HE	6.70	7.00	7.30	0.264	0.276	0.287
θ	0°	-	10°	0°	-	10°

STYLE 1:
PIN 1. BASE
2. COLLECTOR
3. EMITTER
4. COLLECTOR

SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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